

Last Search in paper no. 13

L Number	Hits	Search Text	DB	Time stamp
-	795	split adj gate and (interdielectric layer idl) with oxide with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:00
-	0	split adj gate and (interdielectric adj layer idl) with oxide with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 19:28
-	0	split adj gate and (interdielectric adj layer idl) with oxide with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 19:28
-	2	split adj gate and (inter adj dielectric adj layer idl) with oxide with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 19:28
-	2	jp-06163522-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/17 19:31
-	0	(conventional typical) adj thickness with thin adj silicon adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:00
-	0	(conventional typical) adj thicknesses with thin adj silicon adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:00
-	821	thin adj silicon adj oxide adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:01
-	151	thin adj silicon adj oxide adj layer with thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:01
-	1	thin adj silicon adj oxide adj layer with thickness with (typically conventionally generally usually)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:03
-	12	thin adj silicon adj oxide adj layer with thickness with (typical conventional general usual)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:07
-	0	thin adj silicon adj oxide adj layer with thickness with (common commonly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 09:07